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(71) Applicant (for all designated States except US): **MASSACHUSETTS INSTITUTE OF TECHNOLOGY** [US/US]; 77 Massachussets Avenue, Cambridge, MA 02139 (US).

(72) Inventors; and

(75) Inventors/Applicants (for US only): **LIU, Jifeng** [CN/US]; 6 Bedford Street, Apt. 1R, Somerville, MA 02143 (US). **CANNON, Douglas, D.** [US/US]; 21 Calvin Street, Apr. 3, Somerville, MA 02143 (US). **WADA, Kazumi** [JP/US]; 23 Hill Street, Lexington, MA 02421 (US). **JONGTHANMANURAK, Samerkhea** [US/TH];

Vipavadee 42 Road, Bangkok, Thailand 10900 (TH). **DANNIELSON, David, T.** [US/US]; 265 Elm Street, Apt. 3, Somerville, MA (US). **MICHEL, Jurgén** [DE/US]; 500 Summer Street, Arlington, MA 02474 (US). **KIMERLING, Lionel, C.** [US/US]; 369 Strawberry Hill Road, Concord, MA 01742 (US).

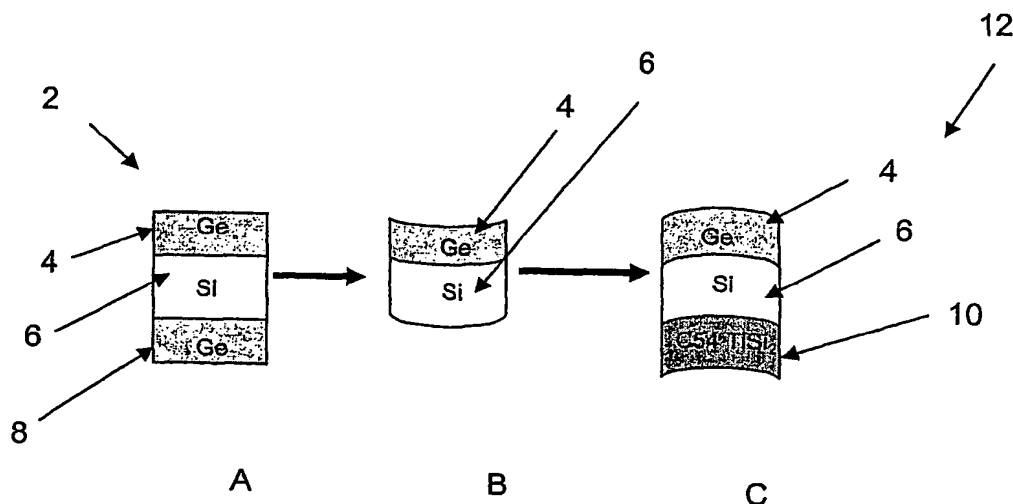
(74) Agents: **CONNORS, Matthew et al.**; Gauthier & Connors LLP, 225 Franklin Street, Suite 3300, Boston, MA 02110 (US).

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(54) Title: METHOD AND STRUCTURE OF STRAIN CONTROL OF SiGe BASED PHOTODETECTORS AND MODULATORS



(57) Abstract: A SiGe or Ge structure comprises a substrate and a SiGe or Ge layer that is formed on a first surface of the substrate. A silicidation or germanide layer is formed on a second surface of the substrate so to increase the tensile strain of the SiGe or Ge layer on the first surface.



SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

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